Channel and parties barrier adj height) near3 adjoxide or aluminum adjoxide) near4 gate   USPAT;   USPAGPUB;   EPO, JPO;   DERWENT;   IBM, TDB   USPAT;   USPAGPUB;   USPAGPUB;   USPAT;   USPAGPUB;   USP					
- 5448 channel near3 hot	•	437	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate	USPAT;	2003/10/10 11:27
. 5448 channel near3 hot hot distribute hot channel near3 hot hot channel near3 hot hot distribute hot channel near3 hot hot channel near3 hot hot distribute hot channel near3 hot hot distribute hot		1			
Language of the control of the cont					
S448   Channel near3 hot   USPAT;   U					
Section   Channel adj hot) and (lantalum titanium zirconium niobium) adj oxide and aluminum adj oxide strain and (floating adj gate non-volatile nonvolatile)   USPAT   USPA				_	
Channel adj hot) and (lantalum titanium zirconium niobium) adj oxide and aluminum adj oxide arm and (floating adj gate non-volatile)	-	5448	channel near3 hot		2003/04/29 14:05
Channel adj hot) and (lantalum titanium zirconium niciblum) adj oxide and aluminum adj oxide   STAN   STA					
Channel adj hot) and (tantalum titanium zirconium nicbium) adj oxide and aluminum   USPAT; USPGPUB   USPAT					
Channel adj hot) and (tantalum titanium ziroonium nichium) adj oxide and aluminum adj exide sard algorithms adj oxide sard aluminum adj exide sard algorithms adj oxide sard aluminum adj exide sard adj exide sard adj exide sard (floating adj gate non-volatile)   157					
adj oxide   U.S.P.GPUB   U.S.				IBM_TDB	
2003/04/29 14:06 271 sram and (floating adj gate non-volatile nonvolatile) 272 sram and (floating adj gate) and (gate non-volatile nonvolatile) 273 silicon 274 (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) (floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) and (floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) and (floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) and (floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) and (floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/315.321).CCLS.))) and (floating adj gate) and 257/3\$2.ccls.) not (floating adj gate) and (g257/3	-	9	(channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum		2003/04/29 14:05
US-PGPUB silicon)  157 (conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3 silicon)  165 (tunnel adj barrier barrier adj height) near3 silicon  166 (tunnel adj barrier barrier adj height) near3 silicon  170 US-PAT. US-PGPUB: EPO: JPO: DERWENT; IBM. TDB USPAT. US-PGPUB: EPO: JPO: USPAT. US-PGPUB: EPO: JPO: DERWENT; IBM. TDB USPAT. US-PGPUB: USPAT. US-PGPUB: EPO: JPO: DERWENT; IBM. TDB USPAT. US-PGPUB: USPAT. US-PGPUB: EPO: JPO: DERWENT; IBM. TDB USPAT. US-PGPUB: USPAT. US-PGPUB: EPO: JPO: DERWENT; IBM. TDB USPAT. US-PGPUB: USPAT. US-PGPUB: USPAT. US-PGPUB: EPO: JPO: DERWENT: IBM. TDB USPAT. US-PGPUB: EPO: JPO: DERWENT: IBM. TDB USPAT. US-PGPUB: EPO: JPO: DERWENT: IBM. TD			adj oxide	US-PGPUB	:
157   (conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3   U.S.PAT.   U.S.PGPUB; EPO; JPO; DERWENT; IBM TIDB USPAT.   U.S.PGPUB; EPO; JPO; IBM TIDB USPAT.   U.S.P	<b> </b> -	6271	sram and (floating adj gate non-volatile nonvolatile)	USPAT;	2003/10/10 11:27
Silicon   Silicon   Silicon   Silicon   Silicon   Silicon   September   Sept	•			US-PGPUB	
Silicon   Silicon   Silicon   Silicon   Silicon   Silicon   September   Sept	-	157	(conduction adj band adj offset) not ((tunnel adj barrier barrier adj height) near3	USPAT;	2003/04/29 14:06
FPO_UPO_DERWENT;			1	US-PGPUB:	
DERWENT:   IBM TDB   USPAT;		ł			ĺ
IBM_TDB					
165   (tunnel adj barrier barrier adj height) near3 silicon   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM, TDB USPAT; US-PGPUB; EPO; JPO; DERWENT, IBM, TDB USPAT; US-PGPUB; EPO; JPO; JPO; IBM, TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J					
USPAT: USPAT: USPAT: USPAT: USPAT: USPAT: USPAT: USPAT: USPGPUB EPO; JPO; DO3/04/29 14:06 USPAT: U	_	165	(tunnel adi harrier harrier adi height) near3 silicon		2003/04/29 14:06
1   work adj function near3 silicon adj dioxide   EPC, JPC; DERWENT; IBM_TDB   USPAT; USPAT;   EPC, JPC; IBM_TDB   USPAT;			(without day battor day the grid thouse of the ori		2000/04/20 14:00
- 1 1 work adj function near3 silicon adj dioxide					
1   work adj function near3 silicon adj dioxide     IBM_TDB   USPAT; US-PGPUB; EPO; JPO; IBM_TDB   USPAT; US-PGPUB; IBM_TDB   USPAT					
1   work adj function near3 silicon adj dioxide					
September   Sep		1	work adi function near? cilicon adi disvida		2002/04/20 44:00
- 6 (((*4271487") or (*4333166") or (*4760556") or (*5042011") or (*5111427") or (*51816385") or (*5280205") or (*5399516") or (*54816739") or (*5424569") or (*5801401") or (*5861306") or (*5807404") or (*58059516") or (*5807404")	-	<b>'</b>	work adj function near3 silicon adj dioxide		2003/04/29 14:06
- 6 (("4271487") or ("4333166") or ("4760556") or ("5042011") or ("5111427") or ("5111427") or ("5153853") or ("5280205") or ("5399516") or ("5418739") or ("5424569") or ("5603011"), PN.) and sram (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric (((floating adj gate) and ((257/315,321), CCLS.))) (((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321), CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide (((((floating adj gate) and ((257/315,321), CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide (((((floating adj gate) and ((257/315,321), CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate (((((floating adj gate) and ((257/315,321), CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate ((((((floating adj gate) and (((257/315,321), CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate ((((((((((((((((((((((((((((((((((((					
6   ((("4271487") or ("4303166") or ("540856") or ("5042011") or ("511427") or ("511427") or ("513853") or ("5200205") or ("5399516") or ("5418739") or ("52424569") or ("5498587") or ("5497494") or ("5619642") or ("559670") or ("5986932") or ("5009011"),PN), and sram ((((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric US-PGPUB ((((floating adj gate) and ((257/315,321).CCLS.))) (((floating adj gate) and 257/3\$2.ccls.) oto (((floating adj gate) and ((257/315,321).CCLS.)))) and ((titanium tantalum niobium zirconium aluminum lead) adj oxide ((257/315,321).CCLS.))) ((((floating adj gate) and 257/3\$2.ccls.) too ((((loating adj gate) and ((257/315,321).CCLS.))))) and ((titanium tantalum niobium zirconium aluminum lead) adj oxide ((257/315,321).CCLS.))) ((((floating adj gate) and 257/3\$2.ccls.) too ((((loating adj gate) and ((257/315,321).CCLS.))))) and ((titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate ((((sram flip-flop flip adj flop) and (((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate ((((sram flip-flop flip adj flop) and (((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium niobium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (((((antalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) ((((antalum titanium zirconium niobium) adj oxide ((((antalum titanium zirconium niobium) adj oxide (((((antalum titanium zirconium niobium) adj oxide ((((((((((((((((((((((((((((((((((((					
C51538537 or ("5280205") or ("549516") or ("5418739") or ("5426599") or ("5801401") or ("5801401") or ("5801401") or ("5805206") or ("5801302") or ("5805206") or ("5805205") or ("5805		_			
C5488587' or ("5497484") or ("5619642") or ("5562785") or ("5796670") or ("5801401") or ("5852306") or ("680991"), PN) and sram (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric US-PGPUB (US-PGPUB US-PGPUB vicconium aluminum lead) adj oxide ((257/315,321).CCLS.))) ((floating adj gate) and 257/3\$2.ccls.) US-PAT; US-PGPUB vicconium aluminum lead) adj oxide ((((10 ting adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium vicconium aluminum lead) adj oxide (((((10 ting adj gate) and ((257/315,321).CCLS.)))) (((((10 ting adj gate) and 257/3\$2.ccls.)	-	6		USPAT	2003/04/29 14:06
- 40  - 40  - ((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide  - 11 tunnel adj barrier near3 silicon adj dioxide  - 124 (((((floating adj gate) and ((257/315,321).CCLS.)))) and ((titanium tantalum niobium zirconium aluminum lead) adj oxide  - 24 (((((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide  - 24 (((((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide)  - 24 (((((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot  - 21 perovskite near3 gate  - 21 perovskite near3 gate  - 31 (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and ((((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 32 (sram flip-flop flip adj flop) and ((((257/314-317,321,324,390,410,411).CCLS.) ((365/149,154,185.01,185.08).CCLS.) and @pd>2002/1203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 34 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  - 35 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  - 34 (channel adj hot) and tantalum adj oxide and aluminum adj oxide					
- 40 (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric ((s-PGPUB (((hannel adj hot adj electron) and oxide) and tunnel) and high adj dielectric (us-PGPUB (us-PGPUB vs-PGPUB vs-PGPU					
- 40 (((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric US-PGPUB US-PAT; US-PGPUB; US-PAT; US-PAT; US-PGPUB; US-PAT; US-PGPUB; US-PAT; US-PGPUB; US-PAT; US-PGPUB; US-PAT; US-PGPUB; US-PAT; US-PA					
- 145 ((((floating adj gate) and ((257/315,321).CCLS.)) ((((floating adj gate) and 257/3\$2.ccls.) not (((floating adj gate) and ((257/315,321).CCLS.)))) and (((tlanium tantalum niobium zirconium aluminum lead) adj oxide  - 1 1 ((((floating adj gate) and ((257/315,321).CCLS.))) (((floating adj gate) and 257/3\$2.ccls.) not (((floating adj gate) and ((257/315,321).CCLS.))) (((floating adj gate) and 257/3\$2.ccls.) not (((floating adj gate) and ((257/315,321).CCLS.)))) and ((tlanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate  - 21 (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tlantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.) (365/149,154,185.01,185.08).CCLS.) and @pd>2003/04/29 14:06  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 ((channel adj hot) and tantalum adj oxide and aluminum adj oxide  USPAT; US-PGPUB EPO; JPO; IBM_TIB USPAT;					
- 145 ((((floating adj gate) and ((257/315,321).CCLS.)) ((((floating adj gate) and 257/3\$2.ccls.) not (((floating adj gate) and ((257/315,321).CCLS.)))) and (((titanium tantalum niobium zirconium aluminum lead) adj oxide  - 1	-	40	(((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric	USPAT;	2003/04/29 14:06
not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide tunnel adj barrier near3 silicon adj dioxide  1 1				US-PGPUB	
zirconium aluminum lead) adj oxide tunnel adj barrier near3 silicon adj dioxide  1 USPAT; US-PGPUB; EPO; JPO; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; IBM_TDB	-	145		USPAT;	2003/04/29 14:06
- 24 ((((floating adj gate) and ((257/315,321).CCLs.)) (((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLs.))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate  - 21 (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLs. (365/149,154,185.01,185.08).CCLs.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO;			not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium	US-PGPUB	
- 24 (((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.) not (((floating adj gate) and ((257/315,321).CCLS.))) (((floating adj gate) and 257/3\$2.ccls.) not (((floating adj gate) and ((257/315,321).CCLS.)))) and ((itanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot  - 21 perovskite near3 gate  - 31 (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and ((((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and ((((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 32 (sram flip-flop flip adj flop) and ((((257/314-317,321,324,390,410,411).CCLS.) ((365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; JPO; IBM_TDB US-PGPUB; EPO; JPO; JPO; IBM_TDB US-PGPUB; EPO; JPO; IBM_TDB US-PGPUB; EPO; JPO; JPO; IBM_TDB US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J			zirconium aluminum lead) adj oxide		
- 24 ((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot  - 21 perovskite near3 gate  - 31 (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 32 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 34 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 35 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  - 36 (((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.  - 36 ((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.  - 37 ((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 38 ((channel adj hot) and tantalum adj oxide and aluminum adj oxide  - 39 ((channel adj hot) and tantalum adj oxide and aluminum adj oxide  - 39 ((channel adj hot) and tantalum adj oxide and aluminum adj oxide	-	1	tunnel adj barrier near3 silicon adj dioxide	USPAT;	2003/04/29 14:06
- 24 ((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate  21				US-PGPUB;	
- 24 ((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate  21				EPO; JPO;	
- 24 ((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.)					
not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate  USPAT; USPGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  ((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  ((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  (channel adj hot) and tantalum adj oxide and aluminum adj oxide  USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB US-PGPUB USPAT; US-PGPUB US-PGPUB US-PGPUB US-PGPUB US-PGPUB US-PGPUB U	-	24	(((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.)		2003/04/29 14:06
zirconium aluminum lead) adj oxide) and channel adj hot perovskite near3 gate  USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  ((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. ((365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  (channel adj hot) and tantalum adj oxide and aluminum adj oxide  (channel adj hot) and tantalum adj oxide and aluminum adj oxide  (channel adj hot) and tantalum adj oxide and aluminum adj oxide  USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB EPO; JPO; IBM_TDB USPAT; US-PGPUB					
- 21 perovskite near3 gate    USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB US-PGPUB USPAT; US-PGPUB US-PGPUB USPAT; US-PGPUB US-PGPUB USPAT; U				: <del>-</del> : <b>-:</b>	
6 ((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  136 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  137 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  138 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  139 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  130 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  139 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  130 (channel adj hot) and tantalum adj oxide and aluminum adj oxide	_	21	1	USPAT:	2003/04/29 14:06
- 135 (sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>2003/04/29 14:06  136 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  137 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  138 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  139 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  130 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  130 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  130 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  130 (channel adj hot) and tantalum adj oxide and aluminum adj oxide		1 -	· · · · · · · · · · · · · · · · · · ·	•	
- 135 (sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide    DERWENT;   IBM_TDB   US-PGPUB;   EPO; JPO;   US-PGPUB;   EPO; JPO;   IBM_TDB   US-PGPUB				•	
- ((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide    IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   IBM_TDB   USPAT;   US-PGPUB   USPAT;   US-PGP					
- ((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  - 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB					
(((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate)  US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB	_	6	((sram flin-flon flin adi flon) and (floating adi gate non-volatile nonvolatile)) and	_	2003/04/20 44-06
- 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide    EPO; JPO;   IBM_TDB   US-PGPUB;   EPO; JPO;   IBM_TDB   USPAT;   US-PGPUB   US-		"			2000/04/28 14.00
- 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide    DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPU			(((amanam aamam zhoomam mobiam) aaj oxide or aluminum aaj oxide) (leal4 gate)	-	
- 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide    IBM_TDB   USPAT;   US-PGPUB;   EPO; JPO;   IBM_TDB   USPAT;   US-PGPUB   USPAT;					
- 135 (sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  - 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide  - 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide  USPAT; US-PGPUB USPA					
(365/149,154,185.01,185.08).CCLS.) and @pd>20021203)  US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB		405	(oram flip flop flip adi flop) and (((057/244-247-204-204-204-204-444) 0.01-2		0000140140 44 00
EPO; JPO; IBM_TDB Channel adj hot) and (tantalum titanium zirconium niobium) adj oxide USPAT; US-PGPUB USPAT; 2003/04/29 14:06 USPAT; 2003/04/29 14:06	-	135			200 <i>3</i> /10/10 11:20
- 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide USPAT; US-PGPUB USPAT; US-PGPUB USPAT; 2003/04/29 14:06			(303/149,134,185.01,185.08).CCLS.) and @pd>20021203)		
- 33 (channel adj hot) and (tantalum titanium zirconium niobium) adj oxide USPAT; US-PGPUB US-PGPUB USPAT; 2003/04/29 14:06					
US-PGPUB USPAT; 2003/04/29 14:06				_	
- 9 (channel adj hot) and tantalum adj oxide and aluminum adj oxide USPAT; 2003/04/29 14:06	-	33	(cnannel adj hot) and (tantalum titanium zirconium niobium) adj oxide		2003/04/29 14:06
		_			
US-PGPUB	-	9	(cnannel adj hot) and tantalum adj oxide and aluminum adj oxide		2003/04/29 14:06
				US-PGPUB	

	609	((conduction adj band adj offset) (((tunnel adj barrier barrier adj height) near3 silicon)	USPAT;	2003/04/29 14:32
1 -	003	and (("5606177").PN.)) (channel adj hot adj electron) ((channel adj hot adj electron)	US-PGPUB;	2000/04/20 14:02
1		and oxide) (((channel adj hot adj electron) and oxide) and tunnel) perovskite ((sram	EPO; JPO;	
		flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) (((sram flip-flop flip	IBM_TDB	
		adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel	IDIVI_IDD	
		adj hot) (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS.) and @pd>20021203) (((tantalum titanium		
		zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot)		
		((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum		
		adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) sram (((US-6141248-\$		
1		or US-6069816-\$).did.) and (insulator insulation insulating gate oxide))		,
		((US-6141248-\$).did.) ((conduction adj band adj offset) not ((tunnel adj barrier barrier		
		adj height) near3 silicon)) (conduction adj band adj offset) (("5606177").PN.)		
		((US-6141248-\$ or US-6069816-\$).did.) ((tunnel adj barrier barrier adj height) near3		
		silicon) "1011" ((((channel adj hot adj electron) and oxide) and tunnel) and high adj		
		dielectric) "1318" (((sram flip-flop flip adj flop) and (floating adj gate non-volatile		
		nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj		
		oxide) near4 gate)) ((US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or		
		US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$		
-		or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or		
		US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$		
		or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or	ļ	
		US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or		
		US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or		
-		US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$		
		or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or		
		US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$	1	
		or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or		
		US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$		
		or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or		
		US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or		
		US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or		
		US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or		
		US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or		
		US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or		
		US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or		
		US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or		
		US-20030038317-\$ or US-20030042553-\$ or US-20030043538-\$ or		
		US-20030043618-\$ or US-20030052371-\$ or US-20030053330-\$).did. or		
		(US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or		
		US-20030067043-\$).did.) ((sram flip-flop flip adj flop) and		
		(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.)		
		and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj	1	
		oxide ) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and		
		@pd>20030415		

	110	(((conduction adi hand adi offcot) (((tunnol adi harriar harriar adi hairaht) near? cilican)	HCDAT.	2003/04/29 14:25
•	416	(((conduction adj band adj offset) (((tunnel adj barrier barrier adj height) near3 silicon) and (("5606177").PN.)) (channel adj hot adj electron) ((channel adj hot adj electron)	USPAT; US-PGPUB;	2003/04/29 14:25
		and oxide) (((channel adj hot adj electron) and oxide) and tunnel) perovskite ((sram	EPO; JPO;	
ı		flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) (((sram flip-flop flip	IBM_TDB	
		adj flop) and (floating adj gate non-volatile nonvolatile)) and @pd>20021203) (channel	15155	
		adj hot) (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS.) and @pd>20021203) (((tantalum titanium		
		zirconium niobium) adj oxide or aluminum adj oxide) near4 gate) (channel near3 hot)		
		((channel adj hot) and (tantalum titanium zirconium niobium) adj oxide and aluminum		
		adj oxide) (sram and (floating adj gate non-volatile nonvolatile)) sram (((US-6141248-\$		
		or US-6069816-\$).did.) and (insulator insulation insulating gate oxide))		
		((US-6141248-\$).did.) ((conduction adj band adj offset) not ((tunnel adj barrier barrier		
		adj height) near3 silicon)) (conduction adj band adj offset) (("5606177").PN.)		
		((US-6141248-\$ or US-6069816-\$).did.) ((tunnel adj barrier barrier adj height) near3		
		silicon) "1011" ((((channel adj hot adj electron) and oxide) and tunnel) and high adj		
		dielectric) "1318" (((sram flip-flop flip adj flop) and (floating adj gate non-volatile		
		nonvolatile)) and (((tantalum titanium zirconium niobium) adj oxide or aluminum adj		
		oxide) near4 gate)) ((US-6501677-\$ or US-6501692-\$ or US-6504765-\$ or		
		US-6504775-\$ or US-6504786-\$ or US-6504788-\$ or US-6507124-\$ or US-6509616-\$		
		or US-6510075-\$ or US-6510076-\$ or US-6528817-\$ or US-6528839-\$ or US-6529397-\$ or US-6529399-\$ or US-6529401-\$ or US-6529403-\$ or US-6529407-\$		
		or US-6529408-\$ or US-6531731-\$ or US-6532169-\$ or US-6534819-\$ or		
		US-6535417-\$ or US-6535442-\$ or US-6535453-\$ or US-6538277-\$ or		
		US-6538338-\$).did. or (US-6542401-\$ or US-6545297-\$ or US-6545311-\$ or		
		US-6545905-\$ or US-6549448-\$ or US-6549449-\$ or US-6549450-\$ or US-6549451-\$		
		or US-6549452-\$ or US-6549453-\$ or US-6549458-\$ or US-6512245-\$ or		
		US-6512691-\$ or US-6512700-\$ or US-6512718-\$ or US-6515894-\$ or US-6515931-\$		
	1	or US-6519176-\$ or US-6519204-\$ or US-6522569-\$ or US-6522582-\$ or		
		US-6522586-\$ or US-6525382-\$ or US-6525962-\$ or US-6525983-\$ or US-6525985-\$		
		or US-6493255-\$).did. or (US-6493256-\$ or US-6493267-\$ or US-6496887-\$ or		
		US-6501127-\$).did. or (US-20020179960-\$ or US-20020179964-\$ or	ŀ	
		US-20020180069-\$ or US-20020181273-\$ or US-20020181274-\$ or		
		US-20020185692-\$ or US-20020186579-\$ or US-20020186580-\$ or		
		US-20020186581-\$ or US-20020190343-\$ or US-20020191436-\$ or		
		US-20020195669-\$ or US-20030002328-\$ or US-20030007380-\$ or		
		US-20030007381-\$ or US-20030012049-\$ or US-20030016554-\$ or		
		US-20030021144-\$ or US-20030026124-\$ or US-20030026150-\$ or		
		US-20030038317-\$ or US-20030042553-\$ or US-20030043538-\$ or US-20030043618-\$ or US-20030053330-\$).did. or	!	
	•	(US-20030058687-\$ or US-20030063485-\$ or US-20030063490-\$ or		
	ļ	US-20030067043-\$).did.) ((sram flip-flop flip adj flop) and		
		(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.)		
	i	and @pd>20021203)) ((channel adj hot) and (tantalum titanium zirconium niobium) adj		
		oxide ) ((channel adj hot) and tantalum adj oxide and aluminum adj oxide)) and		İ
		@pd>20030415) and @pd>20030418		
-	40	(((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.)	USPAT;	2003/04/29 14:26
		and @pd>20030415) and @pd>20030418	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	117	(sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 11:21
		(365/149,154,185.01,185.08).CCLS.) and @pd>20030415)	US-PGPUB;	
			EPO; JPO;	
	4000	(057/044 047 004 004 000 440 444) 001 0 (005/440 454 455 04 455 00) 001 0	IBM_TDB	0000404044
-	4202	(257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and	USPAT;	2003/10/10 11:21
_	47	│ @pd>20030415 │ (sram and (floating adj gate non-volatile nonvolatile)) and	US-PGPUB USPAT;	2003/10/10 11:23
-	4'	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS. and	US-PGPUB	2003/10/10 11.23
		(((237/314-317,321,324,390,410,411).CCE3. (303/149,134,163.01,163.06).CCE3. and @pd>20030415) not dram)	OG-FGFUB	
-	109	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 11:23
		(365/149,154,185.01,185.08). CCLS.) and @pd>20030415)) not ((sram and (floating	US-PGPUB	
		adj gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))	<u></u>	

<b> </b> -	156	((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 11:23
		(365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) ((sram and (floating adj	US-PGPUB	
		gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS.		
	_ :	(365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram))		
-	1530	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/10/10 11:25
		@pd>20030415	US-PGPUB	
-	2008	((conduction adj band adj offset) (((channel adj hot adj electron) and oxide) and	USPAT;	2003/10/10 11:26
		tunnel) (((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	US-PGPUB;	
		@pd>20021203) (channel adj hot) (((tantalum titanium zirconium niobium) adj oxide or	EPO; JPO;	
		aluminum adj oxide) near4 gate) (channel near3 hot) ((channel adj hot) and (tantalum	IBM_TDB	
		titanium zirconium niobium) adj oxide and aluminum adj oxide) (sram and (floating adj		
		gate non-volatile nonvolatile)) ((conduction adj band adj offset) not ((tunnel adj barrier		
		barrier adj height) near3 silicon)) ((tunnel adj barrier barrier adj height) near3 silicon)		
		((((channel adj hot adj electron) and oxide) and tunnel) and high adj dielectric)		
		((((floating adj gate) and ((257/315,321).CCLS.)) (((floating adj gate) and 257/3\$2.ccls.)		
		not ((floating adj gate) and ((257/315,321).CCLS.)))) and (titanium tantalum niobium		
		zirconium aluminum lead) adj oxide) (perovskite near3 gate) ((sram flip-flop flip adj		
		flop) and (((257/314-317,321,324,390,410,411).CCLS.		
		(365/149,154,185.01,185.08).CCLS.) and @pd>20021203)) ((channel adj hot) and		
		(tantalum titanium zirconium niobium) adj oxide ) ((channel adj hot) and tantalum adj		
	70	oxide and aluminum adj oxide)) and @pd>20030418		
-	79	sram and ((365/149,154,185.01,185.08).CCLS.) and @pd>20030415	USPAT;	2003/10/10 11:27
	70	(/265/140 454 405 04 405 00) CCI C \ mat draws and Condo 200405	US-PGPUB	2002/40/40 44:07
-	79	((365/149,154,185.01,185.08).CCLS.) not dram and @pd>20030415	USPAT;	2003/10/10 11:27
			US-PGPUB	00004040404407
-	28	conduction adj band adj offset and @pd>20030415	USPAT;	2003/10/10 11:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	000040404040
-	62	((tantalum titanium zirconium niobium) adj oxide or aluminum adj oxide) near4 gate	USPAT;	2003/10/10 11:27
		and @pd>20030415	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1334	sram and (floating adj gate non-volatile nonvolatile) and @pd>20030415	IBM_TDB	2002/40/40 44:20
[ -	1334	Stath and (noating adjigate non-volatile nonvolatile) and @pd/20050415	USPAT; US-PGPUB	2003/10/10 11:28
	612	sram with (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT;	2003/10/10 11:29
	012	sain with (hoating ad) gate non-volatile nonvolatile) and topo-20050413	US-PGPUB	2003/10/10 11.29
_	1	sram with cmos with (floating adj gate non-volatile nonvolatile) and @pd>20030415	USPAT:	2003/10/10 11:29
	1	saliti with othes with (heating ad) gate non-volatile honvolatile) and topa-2000415	US-PGPUB	2003/10/10 11.29
_	28	conduction adj band adj offset and @pd>20030415	USPAT;	2003/10/10 11:30
-	20	conduction adjudand adjuniset and wpurzousu410	US-PGPUB;	2003/10/10 11.30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	244	perovskite and @pd>20030415	USPAT	2003/10/10 11:30
	6	(sram flip-flop flip adj flop) and (perovskite and @pd>20030415)	USPAT;	2003/10/10 11:31
	]	(	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	216	(((sram flip-flop flip adj flop) and (((257/314-317,321,324,390,410,411).CCLS.	USPAT;	2003/10/10 12:00
		(365/149,154,185.01,185.08).CCLS.) and @pd>20030415)) ((sram and (floating adj	US-PGPUB;	
		gate non-volatile nonvolatile)) and (((257/314-317,321,324,390,410,411).CCLS.	EPO; JPO;	
		(365/149,154,185.01,185.08).CCLS. and @pd>20030415) not dram)))	DERWENT;	
	1	(((365/149,154,185.01,185.08).CCLS.) not dram and @pd>20030415) (sram with	IBM_TDB	
		cmos with (floating adj gate non-volatile nonvolatile) and @pd>20030415) ((sram		
		flip-flop flip adj flop) and (perovskite and @pd>20030415))		
-	28	floating adj gate with low adj tunnel	USPAT;	2003/10/10 12:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

L Number	Hits	Search Text	DB	Time stamp
•	775	sram and ((365/149,154,185.01,185.08).CCLS.)	USPAT;	2003/10/10 11:26
			US-PGPUB	
-	2128	((365/149,154,185.01,185.08).CCLS.) not dram	USPAT;	2003/10/10 11:27
			US-PGPUB	
-	70	(sram and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/10/10 11:22
		(((365/149,154,185.01,185.08).CCLS.) not dram)	US-PGPUB	İ
-	7	"4295150"	USPAT	2002/12/04 16:22
-	10641	floating adj gate	USPAT;	2002/12/05 11:55
			US-PGPUB	
-	1187	(floating adj gate) and ((257/315,321).CCLS.)	USPAT;	2002/12/04 18:10
			US-PGPUB	
-	581	(((floating adj gate) and 257/3\$2.ccls.) not ((floating adj gate) and	USPAT;	2002/12/04 18:40
		((257/315,321).CCLS.))) and tunnel	US-PGPUB	
-	47	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and	USPAT;	2003/04/29 14:26
		@pd>20030415	US-PGPUB:	
		G, v = v · v ·	EPO; JPO;	
1			IBM_TDB	
-	159	conduction adj band adj offset	USPAT;	2003/10/10 11:30
			US-PGPUB;	2000, 10, 10, 11,00
			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
.	883	channel adj hot adj electron	USPAT;	2003/04/29 14:01
_	000	Granner adj not adj electron	US-PGPUB	2003/04/23 14:01
_	767	(channel adj hot adj electron) and oxide	USPAT:	2003/04/29 14:02
_	707	(channel adj not adj electron) and oxide	US-PGPUB	2003/04/23 14.02
_	528	((channel adj hot adj electron) and oxide) and tunnel		2002/04/20 14:02
-	520	(Channel auj not auj electron) and oxide) and turnler	USPAT;	2003/04/29 14:02
	148375	arom fin flor fin adi flor	US-PGPUB	20024040 44:20
-	1403/3	sram flip-flop flip adj flop	USPAT;	2003/10/10 11:30
			US-PGPUB;	
			EPO; JPO;	
l			DERWENT;	
	404057		IBM_TDB	
-	134957	floating adj gate non-volatile nonvolatile	USPAT;	2003/04/29 14:02
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	282896	work adj function near3 silicon dioxide	USPAT;	2003/04/29 14:03
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	4296	perovskite	USPAT	2003/10/10 11:30
-	9715	(sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)	USPAT;	2003/04/29 14:03
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	1316	((sram flip-flop flip adj flop) and (floating adj gate non-volatile nonvolatile)) and	USPAT;	2003/04/29 14:03
		@pd>20021203	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
-	2025	channel adj hot	USPAT;	2003/04/29 14:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	İ		IBM_TDB	
	491	((257/314-317,321,324,390,410,411).CCLS. (365/149,154,185.01,185.08).CCLS.) and	USPAT;	2003/04/29 14:04
	701	@pd>20021203	US-PGPUB;	2000/04/25 14:04
			EPO; JPO;	
			IBM_TDB	